

 $60V, 25A, 14m\Omega$  max. Silicon N Channel Power MOS FET Power Switching

#### Features

- High speed switching
- Capable of 4.5 V gate drive
- Low drive current
- High density mounting

R07DS0076EJ0200

Rev.2.00

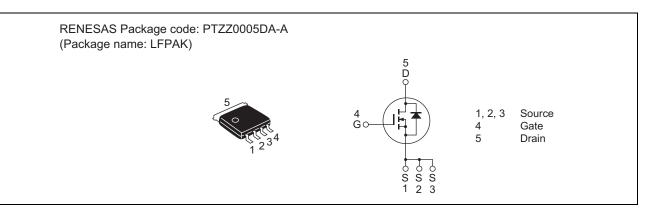
Apr 09, 2013

Low on-resistance

 $R_{DS(on)} = 11 \text{ m}\Omega \text{ typ.}$  (at  $V_{GS} = 10 \text{ V}$ )

- Pb-free
- Halogen-free

#### Outline



## Application

• Switching Mode Power Supply

### **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Ratings	Unit	
Drain to source voltage	V <sub>DSS</sub>	60	V	
Gate to source voltage	V <sub>GSS</sub>	±20	V	
Drain current	Ι <sub>D</sub>	25	А	
Drain peak current	Note1 I <sub>D(pulse)</sub>	100	А	
Body-drain diode reverse drain current	I <sub>DR</sub>	25	А	
Avalanche current	I <sub>AP</sub> Note 2	12.5	А	
Avalanche energy	E <sub>AS</sub> Note 2	11.7	mJ	
Channel dissipation	Pch Note3	45	W	
Channel to Case Thermal Resistance	θch-C	2.78	°C/W	
Channel temperature	Tch	150	٥°	
Storage temperature	Tstg	-55 to +150	٥C	

Notes: 1.  $PW \le 10 \ \mu s$ , duty cycle  $\le 1\%$ 

2. Value at Tch = 25°C, Rg  $\geq$  50  $\Omega$ 

3. Tc = 25°C

This product is for the low voltage drive ( $\leq 10$ V).

If the driving voltage is over 10 V under normal conditions, please use the product for high gate to source cutoff voltage  $(V_{GS(off)})$  which characteristics has been improved.



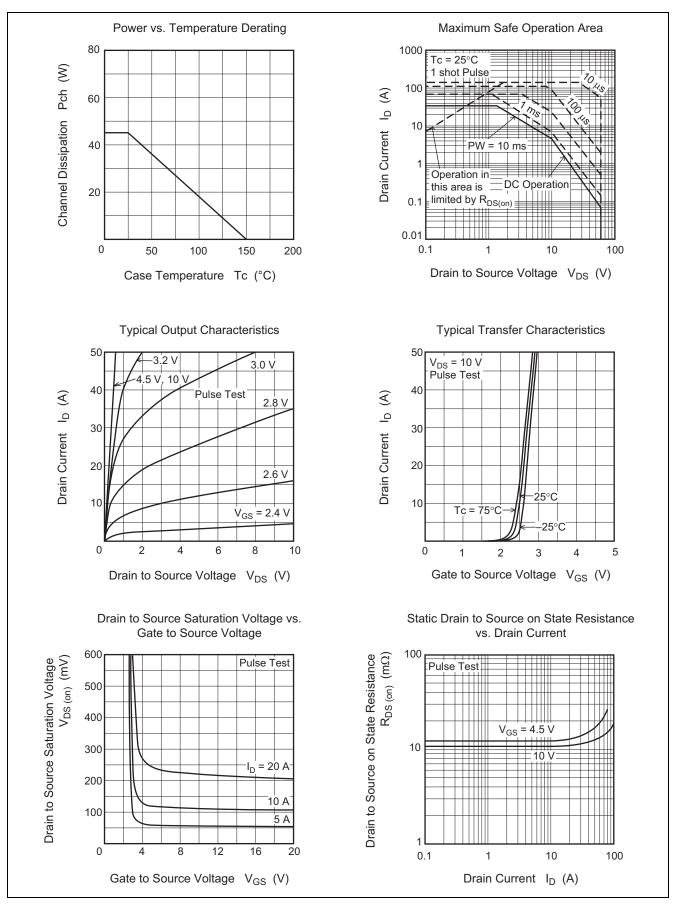
# **Electrical Characteristics**

Item	Symbol	Min	Tun	Max	Unit	(Ta = 25°C) Test Conditions
			Тур	IVIAX		
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	60	—		V	$I_{D} = 10 \text{ mA}, V_{GS} = 0 \text{ V}$
Gate to source leak current	I <sub>GSS</sub>	_	—	±0.1	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$
Zero gate voltage drain current	I <sub>DSS</sub>	_	—	1	μA	$V_{DS} = 60 V, V_{GS} = 0 V$
Gate to source cutoff voltage	V <sub>GS(off)</sub>	1.2	—	2.5	V	$V_{DS} = 10 V, I_D = 1 mA$
Static drain to source on state	R <sub>DS(on)</sub>	—	11	14	mΩ	$I_D = 12.5 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note4}}$
resistance	R <sub>DS(on)</sub>	_	13	18	mΩ	$I_D = 12.5 \text{ A}, V_{GS} = 4.5 \text{ V}^{Note4}$
Forward transfer admittance	y <sub>fs</sub>	_	40	_	S	$I_D = 12.5 \text{ A}, V_{DS} = 10 \text{ V}^{Note4}$
Input capacitance	Ciss	_	2030	_	pF	$V_{DS} = 10 V, V_{GS} = 0 V,$ f = 1 MHz
Output capacitance	Coss	_	250	_	pF	
Reverse transfer capacitance	Crss	_	100	_	pF	
Gate Resistance	Rg	_	0.7	_	Ω	
Total gate charge	Qg	_	15	_	nC	$V_{DD} = 25 \text{ V}, V_{GS} = 4.5 \text{ V},$ $I_D = 25 \text{ A}$
Gate to source charge	Qgs	_	6.7	_	nC	
Gate to drain charge	Qgd	_	3.7	_	nC	
Turn-on delay time	t <sub>d(on)</sub>	_	8.4	_	ns	$\label{eq:VGS} \begin{array}{l} V_{\text{GS}} = 10 \; V, \; I_{\text{D}} = 12.5 \; A, \\ V_{\text{DD}} \cong 30 \; V, \; R_{\text{L}} = 2.4 \; \Omega, \\ Rg = 4.7 \; \Omega \end{array}$
Rise time	tr	_	4.4	_	ns	
Turn-off delay time	t <sub>d(off)</sub>	_	42	_	ns	
Fall time	t <sub>f</sub>	_	6.8	_	ns	
Body-drain diode forward voltage	$V_{DF}$	_	0.83	1.1	V	$I_F = 25 \text{ A}, V_{GS} = 0 \text{ V}^{Note4}$
Body–drain diode reverse recovery time	t <sub>rr</sub>	_	32	_	ns	$I_F = 25 \text{ A}, V_{GS} = 0 \text{ V}$ $di_F/dt = 100 \text{ A}/\mu \text{s}$

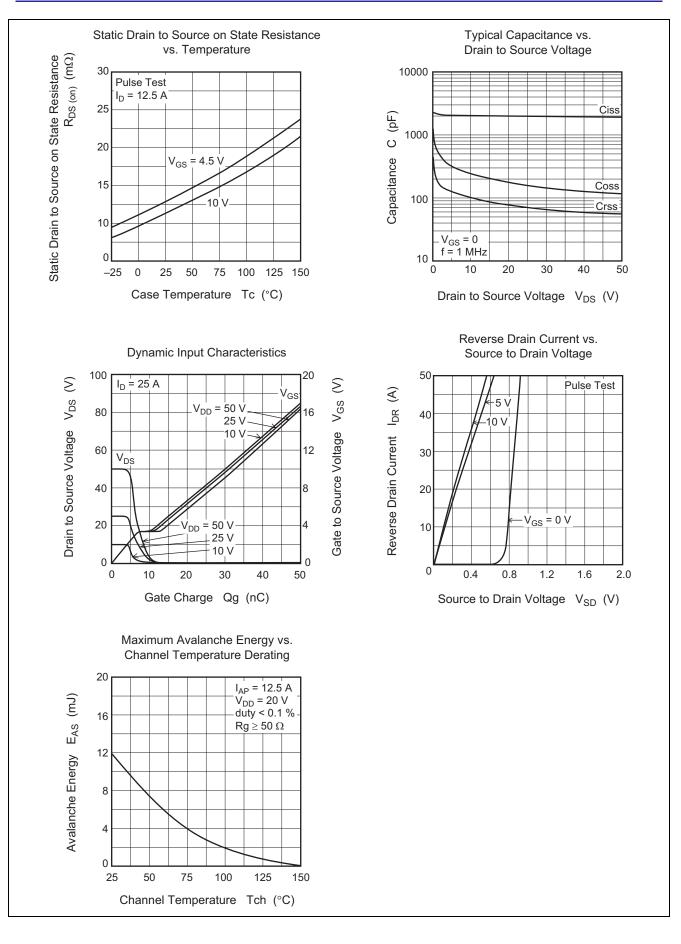
Notes: 4. Pulse test

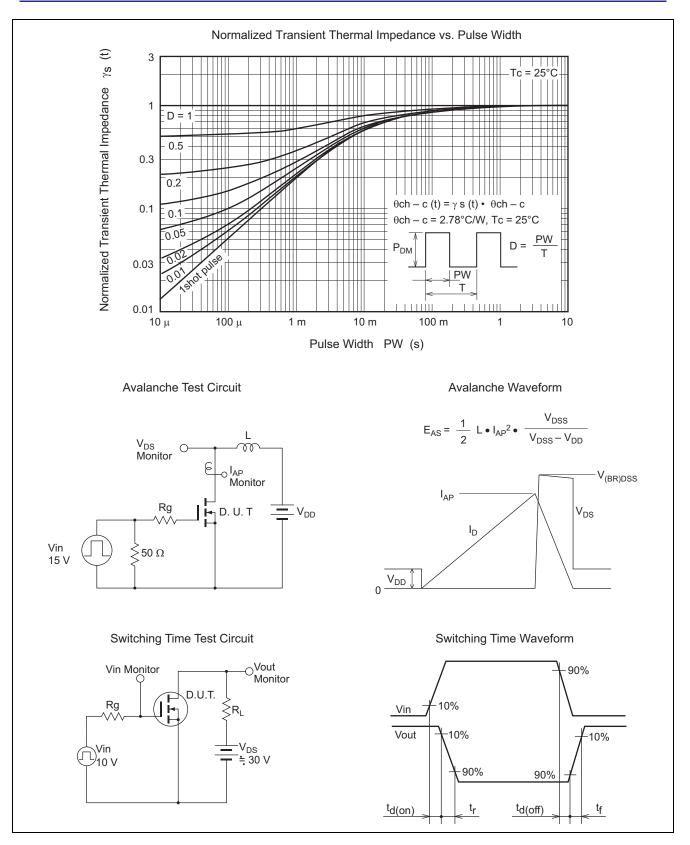


#### **Main Characteristics**



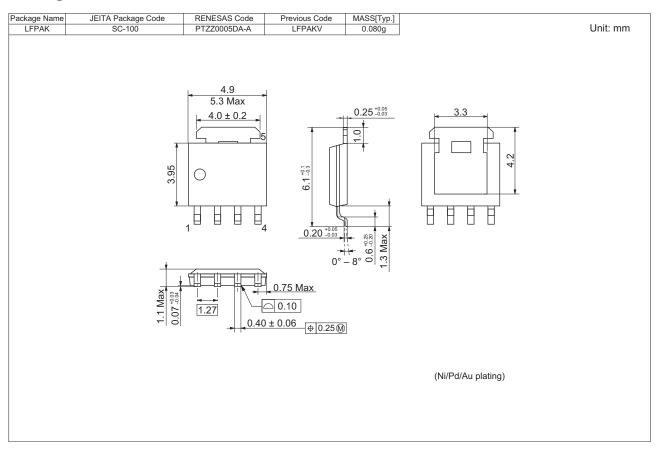








### **Package Dimensions**



### **Ordering Information**

Part No.	Quantity	Shipping Container
RJK0651DPB-00-J5	2500 pcs	Taping



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